



SLPS209A - AUGUST 2009 - REVISED MAY 2010

P-Channel NexFET™ Power MOSFET

Check for Samples: CSD23201W10

FEATURES

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- Ultra Low Qg and Qgd
- Small Footprint 1mm × 1mm
- Low Profile 0.62mm Height
- Pb Free
- Gate ESD Protection 3kV
- RoHS Compliant
- Halogen Free

APPLICATIONS

- Battery Management
- Load Switch
- Battery Protection

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

Top View

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PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	-12		V
Qg	Gate Charge Total (4.5V)	1.8	nC	
Q _{gd}	Gate Charge Gate to Drain	0.26		nC
10.	7	$V_{GS} = -1.5V$	110	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V$	77	mΩ
No.		V _{GS} = -4.5V 66		mΩ
V _{GS(th)}	Threshold Voltage	-0.6		V

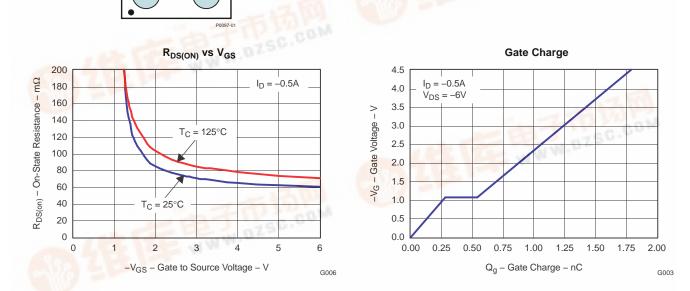
ORDERING INFORMATION

Device Package		Media	Qty	Ship
CSD23201W10	1 × 1 Wafer Level Package	7-inch reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5° <mark>C unless ot</mark> he <mark>rwise st</mark> ated	VALUE	UNIT
V _{DS}	Drain to Source Voltage	-12	V
V _{GS}	Gate to Source Voltage	-6	V
ID	Continuous Drain Current, $T_C = 25^{\circ}C^{(1)}$	-2.2	А
I_{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	-8.8	А
	Continuous Gate Clamp Current	-0.5	А
I _G	Pulsed Gate Clamp Current	-7	А
PD	Power Dissipation ⁽¹⁾	1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	<mark>-55 to</mark> 150	°C

(1) $R_{\theta JA} = 100^{\circ}$ C/W on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB. (2) Pulse width ≤300µs, duty cycle ≤2%



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics	L				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-12			V
BV GSS	Gate to Source Voltage;	$V_{DS} = 0V, I_{G} = -250\mu A$	-6.1		-7.2	V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = -9.6V$			-1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = -6V$			-100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.6	-1.0	V
		$V_{GS} = -1.5V, I_D = -0.5A$		110	138	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -0.5A$		77	96	mΩ
		$V_{GS} = -4.5V, I_D = -0.5A$		66	82	mΩ
g _{fs}	Transconductance	$V_{DS} = -6.0V, I_D = -0.5A$		9		S
Dynamic	c Characteristics					
C _{ISS}	Input Capacitance			250	325	pF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{DS} = -6.0V, f = 1MHz$		125	155	pF
C _{RSS}	Reverse Transfer Capacitance			32	42	pF
Qg	Gate Charge Total (-4.5V)			1.8	2.4	nC
Q _{gd}	Gate Charge Gate to Drain	$V_{DS} = -6.0V. I_D = -0.5A$		0.26		nC
Q_gs	Gate Charge Gate to Source	$v_{\rm DS} = -0.0v, i_{\rm D} = -0.5A$		0.28		nC
Q _{g(th)}	Gate Charge at Vth			0.11		nC
Q _{OSS}	Output Charge	$V_{DS} = -6.0V, V_{GS} = 0V$		1.7		nC
t _{d(on)}	Turn On Delay Time			24		ns
t _r	Rise Time	$V_{DS} = -6.0V, V_{GS} = -2.5V, I_{D} = -0.5A$		19		ns
t _{d(off)}	Turn Off Delay Time	$R_{G} = 20\Omega$		68		ns
t _f	Fall Time			29		ns
Diode C	haracteristics					
V _{SD}	Diode Forward Voltage	$I_{S} = -0.5A, V_{GS} = 0V$		-0.77	-1.0	V
Q _{rr}	Reverse Recovery Charge	V_{dd} = -4.0V, I _F = -0.5A, di/dt = 100A/µs		2		nC
t _{rr}	Reverse Recovery Time	V_{dd} = -4.0V, I _F = -0.5A, di/dt = 100A/µs		9.5		ns

THERMAL CHARACTERISTICS

($T_A = 25^{\circ}C$ unless otherwise stated)

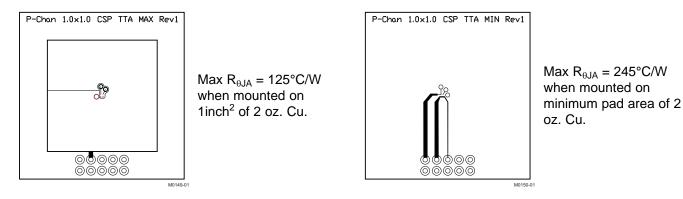
	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Ambient (Minimum Cu area)			245	°C/W
R $_{\theta JA}$	Thermal Resistance Junction to Ambient (1 in ² Cu area)			125	°C/W



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TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

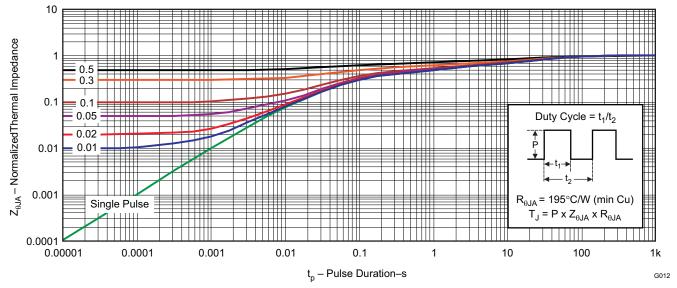


Figure 1. Transient Thermal Impedance

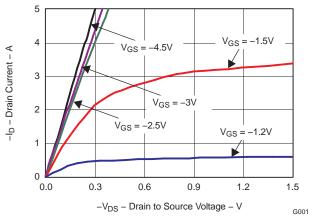
Texas Instruments

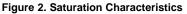
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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$





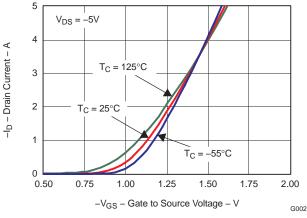


Figure 3. Transfer Characteristics

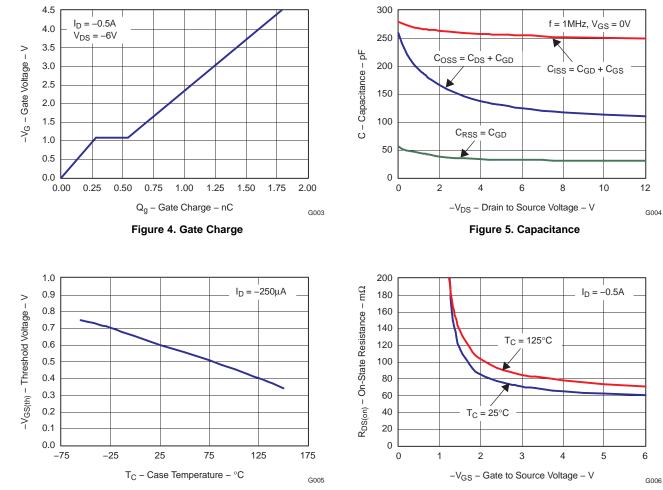


Figure 6. Threshold Voltage vs. Temperature

Figure 7. On Resistance vs. Gate Voltage



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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

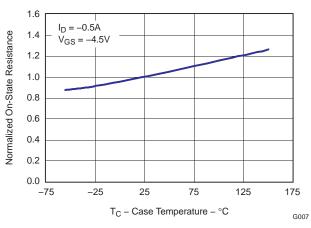


Figure 8. On Resistance vs. Temperature

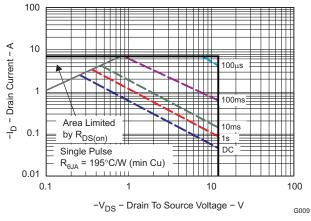


Figure 10. Maximum Safe Operating Area

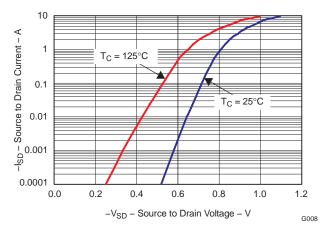


Figure 9. Typical Diode Forward Voltage

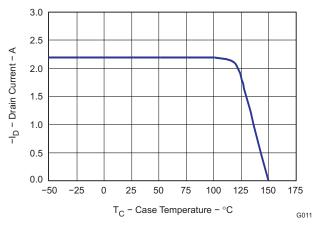


Figure 11. Maximum Drain Current vs. Temperature

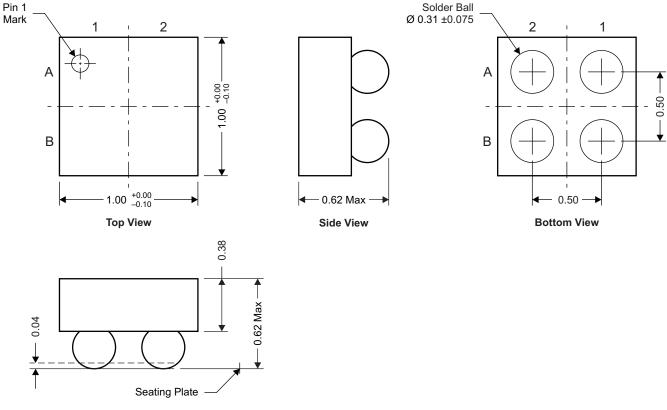
EXAS INSTRUMENTS

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MECHANICAL DATA

CSD23201W10 Package Dimensions



Front View

M0151-01

NOTE: All dimensions are in mm (unless otherwise specified)

Pin Configuration Table

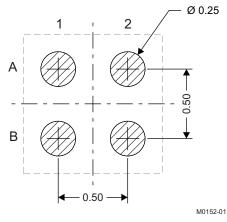
POSITION	DESIGNATION
B1	Source
A1	Gate
A2, B2	Drain



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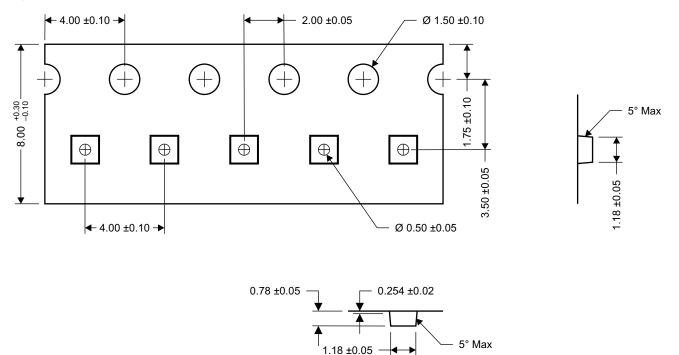
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Land Pattern Recommendation



NOTE: All dimensions are in mm (unless otherwise specified)

Tape and Reel Information



M0153-01

NOTE: All dimensions are in mm (unless otherwise specified)

REVISION HISTORY

Changes from Original (August 2009) to Revision A			
•	Deleted the Package Marking Information section	7	



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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Pe
CSD23201W10	ACTIVE	DSBGA	YZB	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new **PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www. information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retard in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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